



Vincotech

10-FU094PB017ME05-L620F31

datasheet

fastPACK 0 SiC

900 V / 17 mΩ

Features

- 900V SiC MOS
- Switching frequency up to 400kHz
- Suitable for hard switching/soft switching
- Increased power density
- NTC

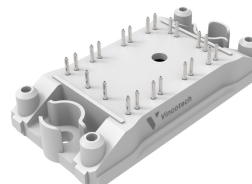
Target applications

- Power Supply
- Special Application
- Welding & Cutting

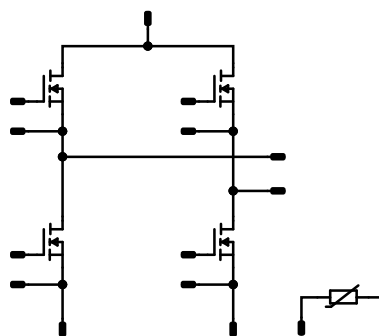
Types

- 10-FU094PB017ME05-L620F31

flow 0 12 mm housing



Schematic





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Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
H-Bridge Switch - Lo side				
Drain-source voltage	V_{DS}		900	V
Drain current	I_D	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	57	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	270	A
Avalanche energy, single pulse	E_{AS}	$V_{DD} = 50\text{ V}$ $I_D = 66\text{ A}$	330	mJ
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	101	W
Gate-source voltage	V_{GS}		-4 / 15	V
		dynamic	-8 / 19	
Maximum Junction Temperature	T_{jmax}		175	°C

H-Bridge Switch - Hi side

Drain-source voltage	V_{DS}		900	V
Drain current	I_D	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	57	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	270	A
Avalanche energy, single pulse	E_{AS}	$V_{DD} = 50\text{ V}$ $I_D = 66\text{ A}$	330	mJ
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	101	W
Gate-source voltage	V_{GS}		-4 / 15	V
		dynamic	-8 / 19	
Maximum Junction Temperature	T_{jmax}		175	°C



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Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
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Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+(T_{jmax} - 25)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	6000	V
Isolation voltage	V_{isol}	AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			min. 12,7	mm
Clearance			9,52	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

H-Bridge Switch - Lo side

Static

Drain-source on-state resistance	$r_{DS(on)}$		15		114	25 125 150		23 28 31	26 ⁽¹⁾	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,015	25	1,7	2,4	3,5	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		30	750	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	900		25		3	300	μA
Internal gate resistance	r_g							1,57		Ω
Gate charge	Q_g		-4/15	400	60	25		91,2		nC
Gate to source charge	Q_{GS}							22,5		
Gate to drain charge	Q_{GD}							36		
Short-circuit input capacitance	C_{iss}	$f = 1 \text{ Mhz}$	0	600	0	25		1980		pF
Short-circuit output capacitance	C_{oss}							180		
Reverse transfer capacitance	C_{rss}							12		
Diode forward voltage	V_{SD}		0		0	25		4,8		V

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4 \text{ W/mK}$ (PSX)						0,94		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 2 \Omega$ $R_{goff} = 2 \Omega$	-5/15	600	60	25 125 150		15,2 14,2 15,2		ns
Rise time	t_r					25 125 150		6,8 6,2 6,2		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		47,2 48,4 46,8		ns
Fall time	t_f					25 125 150		11,4 11,8 10,2		ns
Turn-on energy (per pulse)	E_{on}					25 125 150		0,681 0,607 0,618		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,153 0,101 0,095		mWs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

H-Bridge Switch - Hi side

Static

Drain-source on-state resistance	$r_{DS(on)}$		15		114	25 125 150		23 28 31	26 ⁽¹⁾	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,015	25	1,7	2,4	3,5	V
Gate to Source Leakage Current	I_{GSS}		15	0		25		30	750	nA
Zero Gate Voltage Drain Current	I_{DSS}		0	900		25		3	300	μA
Internal gate resistance	r_g							1,57		Ω
Gate charge	Q_g	-4/15	400	60	25			91,2		nC
Gate to source charge	Q_{GS}							22,5		
Gate to drain charge	Q_{GD}							36		
Short-circuit input capacitance	C_{iss}	f = 1 Mhz	0	600	0	25		1980		pF
Short-circuit output capacitance	C_{oss}							180		
Reverse transfer capacitance	C_{rss}							12		
Diode forward voltage	V_{SD}		0		0	25		4,8		V

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						0,94		K/W
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Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 2 \Omega$ $R_{goff} = 2 \Omega$	-5/15	600	60	25 125 150		15,2 14,2 15,2		ns
Rise time	t_r					25 125 150		6,8 6,2 6,2		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		47,2 48,4 46,8		ns
Fall time	t_f					25 125 150		11,4 11,8 10,2		ns
Turn-on energy (per pulse)	E_{on}					25 125 150		0,681 0,607 0,618		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,153 0,101 0,095		mWs



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Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	

Thermistor

Static

Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	$R_{100} = 1484 \Omega$				100	-5		5	%
Power dissipation	P							5		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. $\pm 1 \%$						3962		K
B-value	$B_{(25/100)}$	Tol. $\pm 1 \%$						4000		K
Vincotech Thermistor Reference									I	

⁽¹⁾ Value at chip level

⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.



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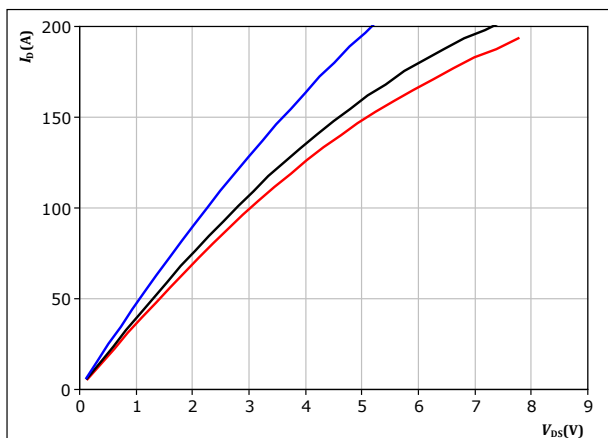
H-Bridge Switch - Lo side Characteristics

figure 1.

MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$



$t_p = 250 \mu s$
 $V_{GS} = 15 V$

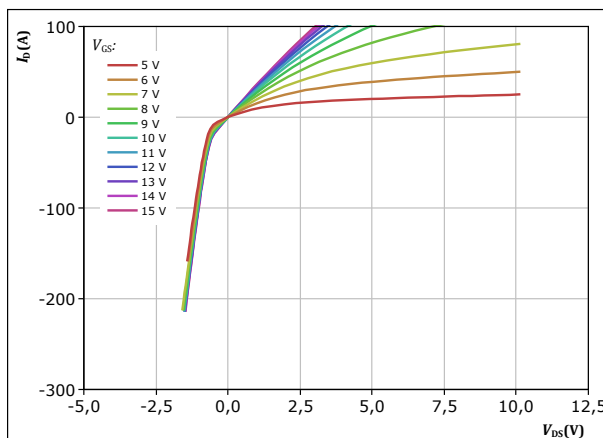
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 2.

MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$



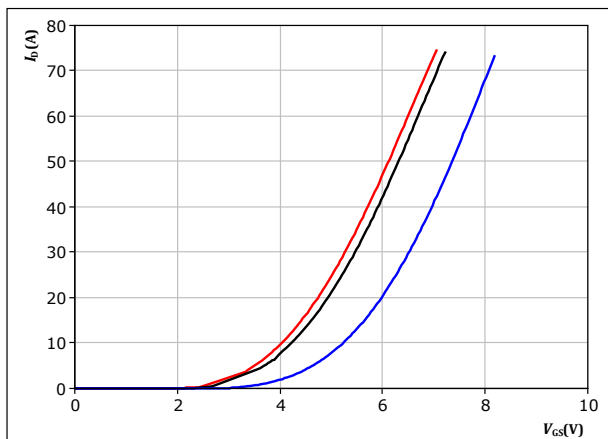
$t_p = 250 \mu s$
 $T_j = 150 \text{ °C}$
 V_{GS} from 5 V to 15 V in steps of 1 V

figure 3.

MOSFET

Typical transfer characteristics

$$I_D = f(V_{GS})$$



$t_p = 250 \mu s$
 $V_{DS} = 10 V$

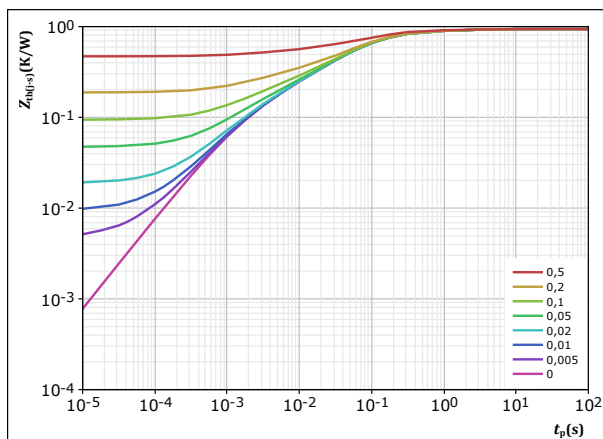
T_j :
— 25 °C
— 125 °C
— 150 °C

figure 4.

MOSFET

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 0,94 \text{ K/W}$
MOSFET thermal model values

$R \text{ (K/W)}$	$\tau \text{ (s)}$
4,21E-02	2,99E+00
1,28E-01	4,21E-01
5,28E-01	7,51E-02
1,69E-01	9,86E-03
7,30E-02	1,37E-03



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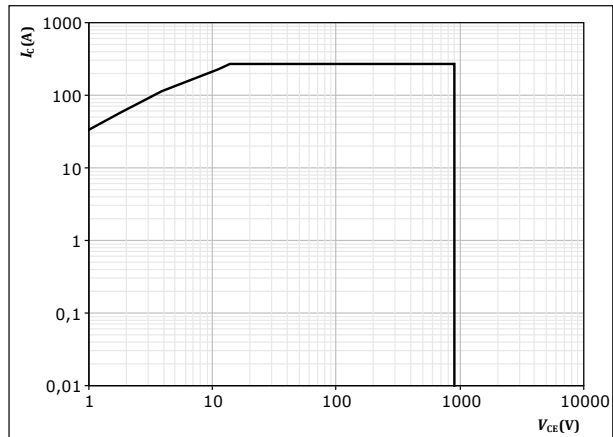
H-Bridge Switch - Lo side Characteristics

figure 5.

MOSFET

Safe operating area

$$I_C = f(V_{CE})$$



$D = \text{single pulse}$

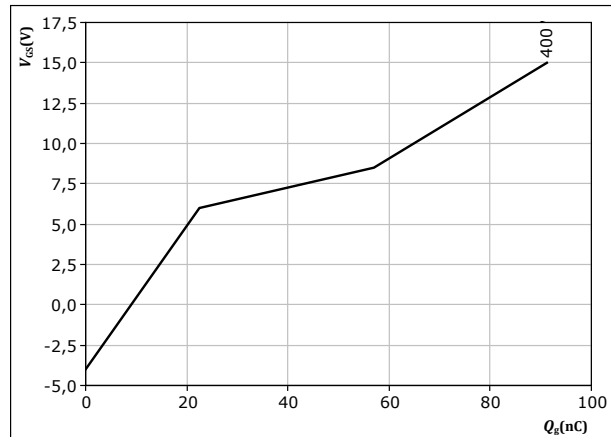
$T_s = 80 \text{ } ^\circ\text{C}$
 $V_{GE} = 15 \text{ V}$
 $T_j = T_{jmax}$

figure 6.

MOSFET

Gate voltage vs gate charge

$$V_{GS} = f(Q_g)$$



At $I_D = 60 \text{ A}$



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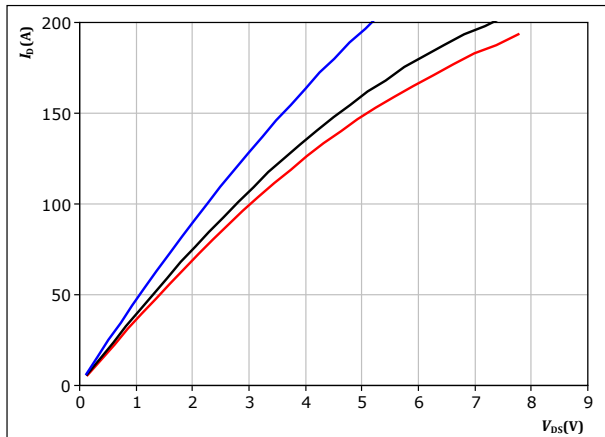
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H-Bridge Switch - Hi side Characteristics

figure 7. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

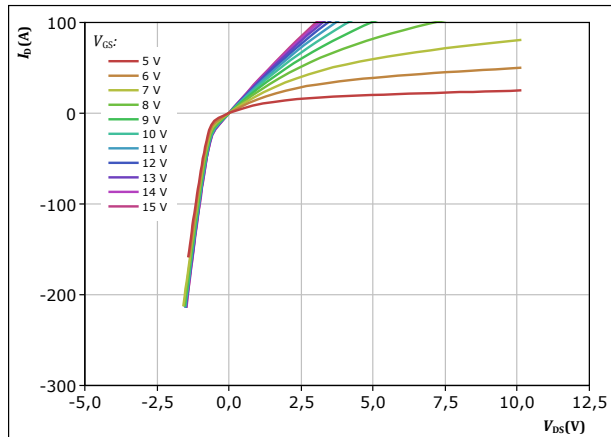


$t_p = 250 \mu s$
 $V_{GS} = 15 V$
 $T_j:$ 25 °C, 125 °C, 150 °C

figure 8. MOSFET

Typical output characteristics

$$I_D = f(V_{DS})$$

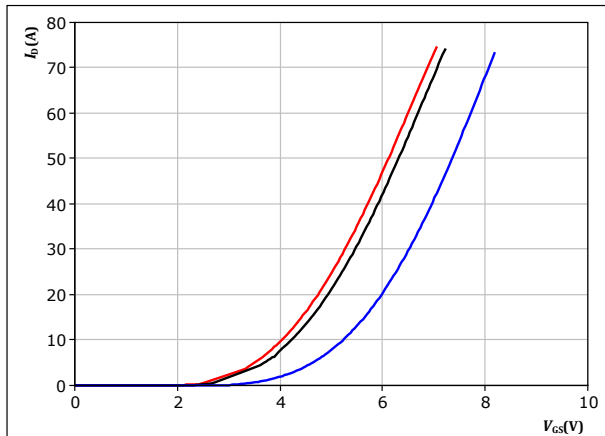


$t_p = 250 \mu s$
 $T_j = 150 ^\circ C$
 V_{GS} from 5 V to 15 V in steps of 1 V

figure 9. MOSFET

Typical transfer characteristics

$$I_D = f(V_{GS})$$

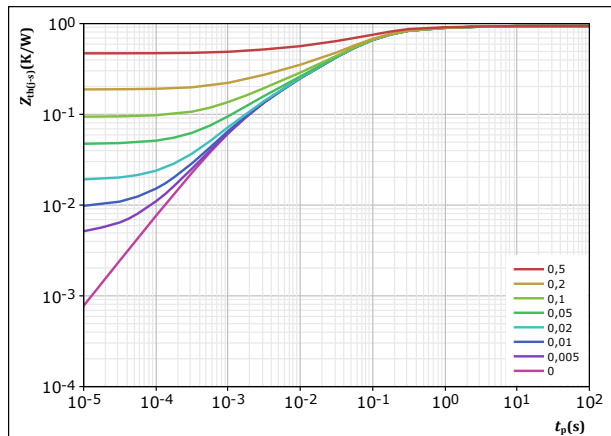


$t_p = 250 \mu s$
 $V_{DS} = 10 V$
 $T_j:$ 25 °C, 125 °C, 150 °C

figure 10. MOSFET

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 0,94 K/W$
MOSFET thermal model values

$R (K/W)$	$\tau (s)$
4,21E-02	2,99E+00
1,28E-01	4,21E-01
5,28E-01	7,51E-02
1,69E-01	9,86E-03
7,30E-02	1,37E-03



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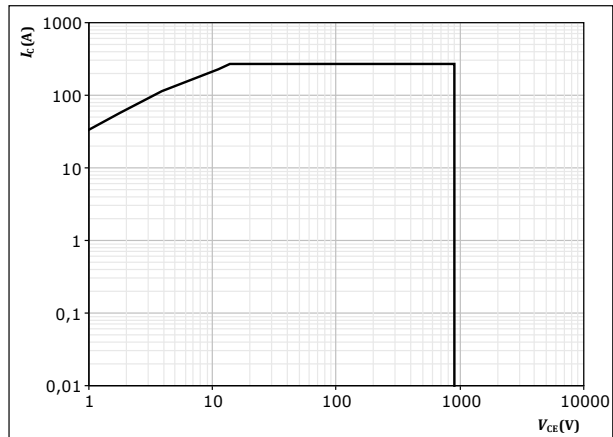
10-FU094PB017ME05-L620F31 datasheet

H-Bridge Switch - Hi side Characteristics

figure 11. MOSFET

Safe operating area

$$I_C = f(V_{CE})$$

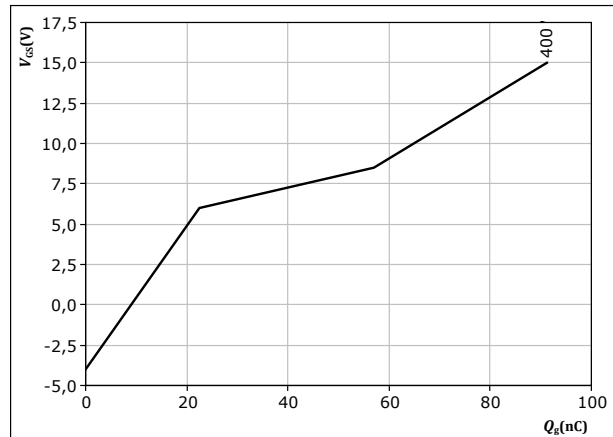


$D = \text{single pulse}$
 $T_s = 80 \text{ } ^\circ\text{C}$
 $V_{GE} = 15 \text{ V}$
 $T_j = T_{jmax}$

figure 12. MOSFET

Gate voltage vs gate charge

$$V_{GS} = f(Q_g)$$



At $I_D = 60 \text{ A}$



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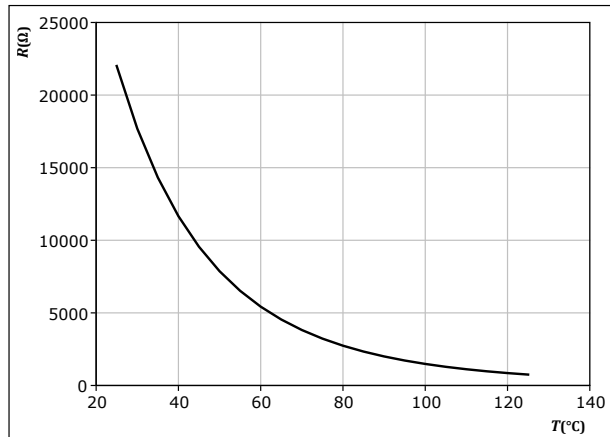
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datasheet

Thermistor Characteristics

figure 13. Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$





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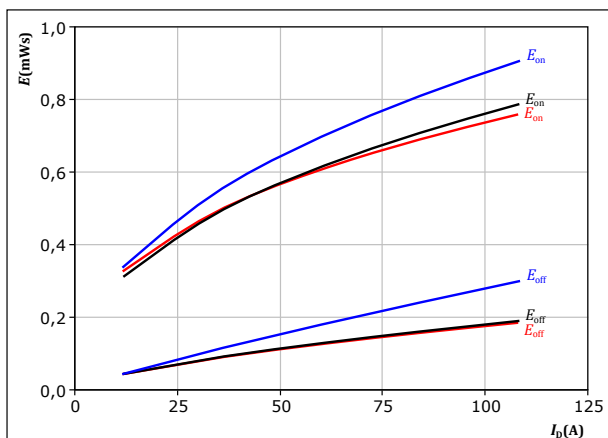
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H-Bridge Switching Characteristics - Lo side

figure 14. MOSFET

Typical switching energy losses as a function of drain current

$$E = f(I_D)$$



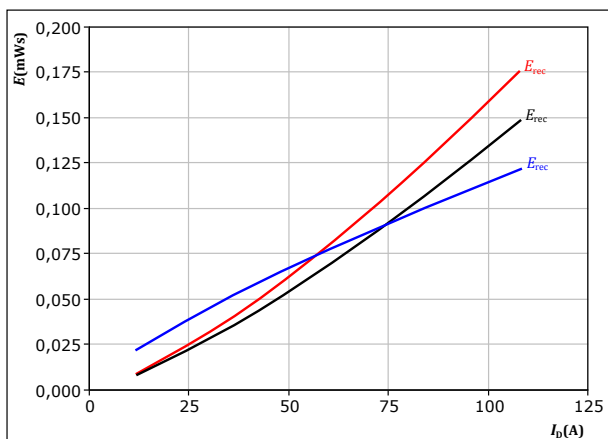
With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-5/15	V		125 °C
$R_{gon} =$	2	Ω		150 °C
$R_{goff} =$	2	Ω		

figure 16. MOSFET

Typical reverse recovered energy loss as a function of drain current

$$E_{rec} = f(I_D)$$



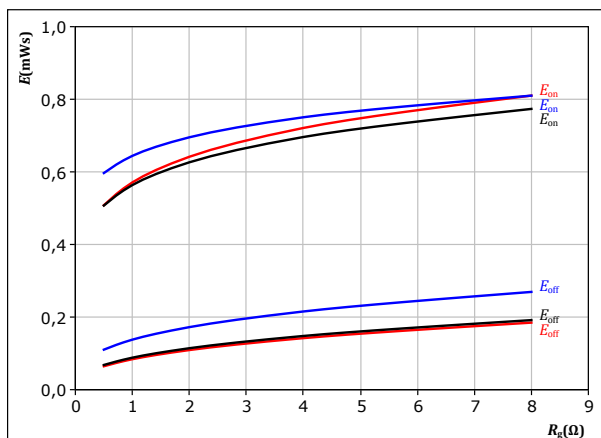
With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-5/15	V		125 °C
$R_{gon} =$	2	Ω		150 °C

figure 15. MOSFET

Typical switching energy losses as a function of gate resistor

$$E = f(R_g)$$



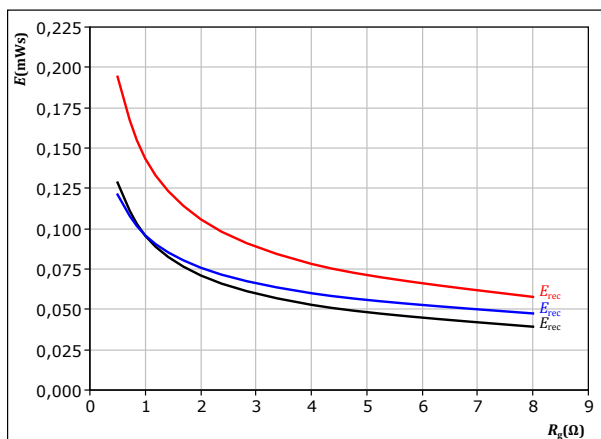
With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-5/15	V		125 °C
$I_D =$	60	A		150 °C

figure 17. MOSFET

Typical reverse recovered energy loss as a function of gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{DS} =$	600	V	$T_j:$	25 °C
$V_{GS} =$	-5/15	V		125 °C
$I_D =$	60	A		150 °C



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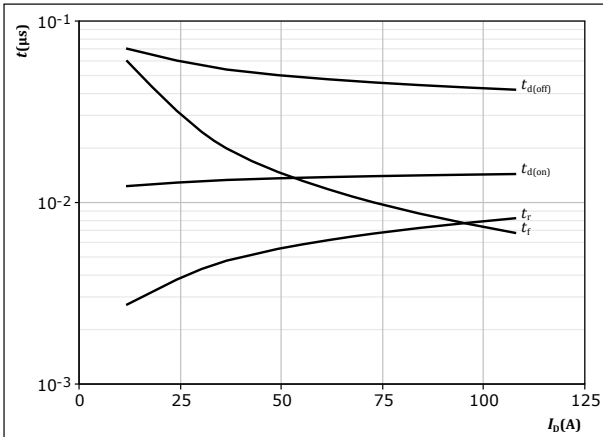
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datasheet

H-Bridge Switching Characteristics - Lo side

figure 18.

MOSFET

Typical switching times as a function of drain current
 $t = f(I_D)$



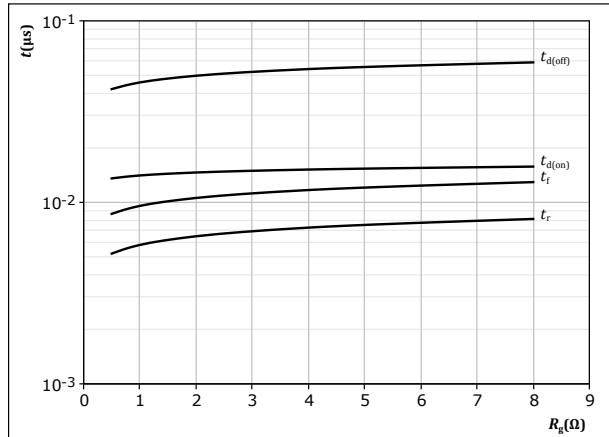
With an inductive load at

$T_j = 150$ °C
 $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 $R_{goff} = 2$ Ω

figure 19.

MOSFET

Typical switching times as a function of gate resistor
 $t = f(R_g)$



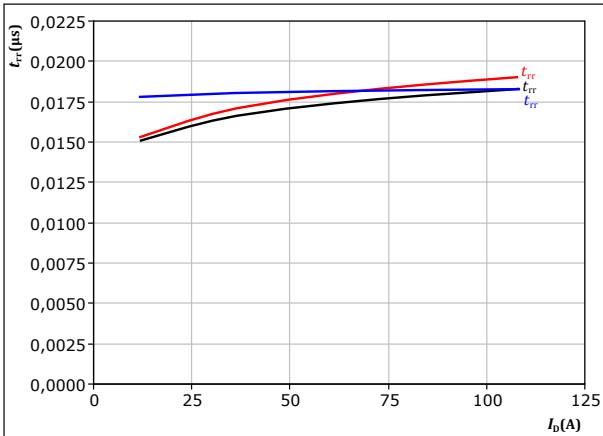
With an inductive load at

$T_j = 150$ °C
 $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A

figure 20.

MOSFET

Typical reverse recovery time as a function of drain current
 $t_{rr} = f(I_D)$

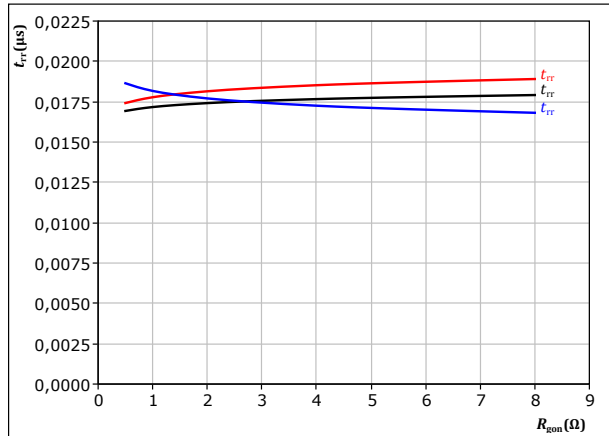


At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 $T_j: 25$ °C (blue)
 125 °C (black)
 150 °C (red)

figure 21.

MOSFET

Typical reverse recovery time as a function of turn on gate resistor
 $t_{rr} = f(R_{gon})$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 $T_j: 25$ °C (blue)
 125 °C (black)
 150 °C (red)



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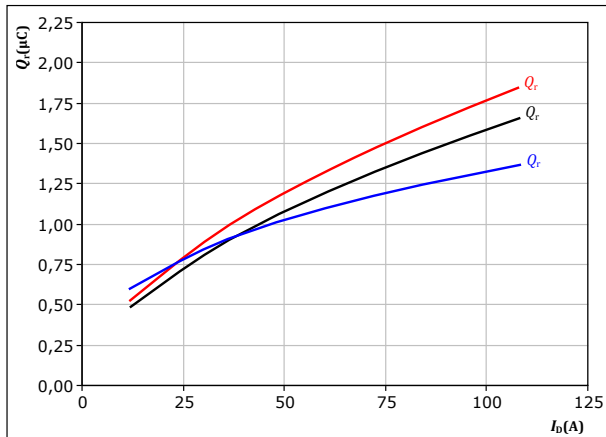
H-Bridge Switching Characteristics - Lo side

figure 22.

MOSFET

Typical recovered charge as a function of drain current

$$Q_r = f(I_D)$$



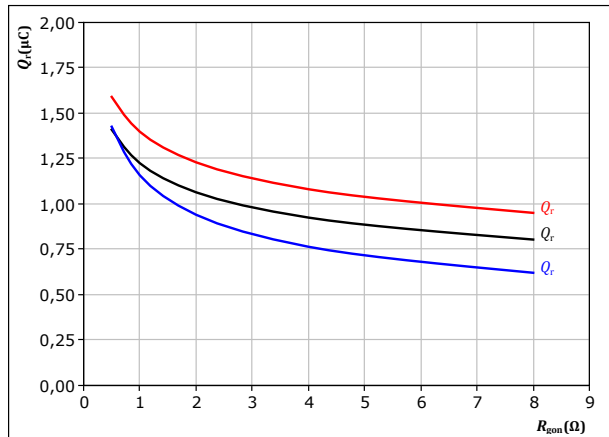
At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 T_j : 25 °C
125 °C
150 °C

figure 23.

MOSFET

Typical recovered charge as a function of turn on gate resistor

$$Q_r = f(R_{gon})$$



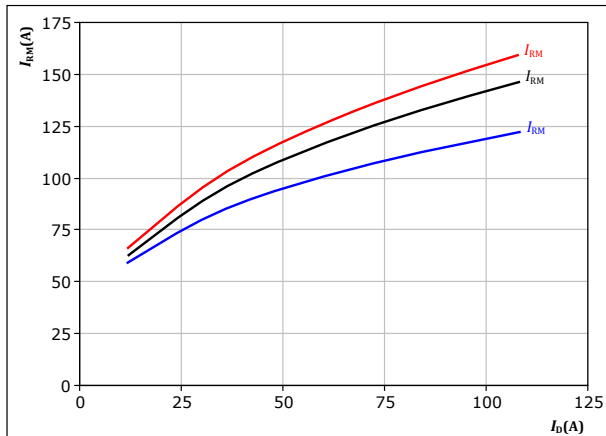
At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 T_j : 25 °C
125 °C
150 °C

figure 24.

MOSFET

Typical peak reverse recovery current as a function of drain current

$$I_{RM} = f(I_D)$$



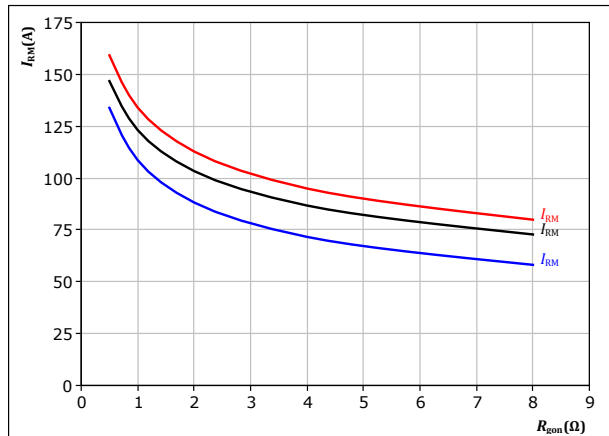
At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 T_j : 25 °C
125 °C
150 °C

figure 25.

MOSFET

Typical peak reverse recovery current as a function of turn on gate resistor

$$I_{RM} = f(R_{gon})$$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 T_j : 25 °C
125 °C
150 °C



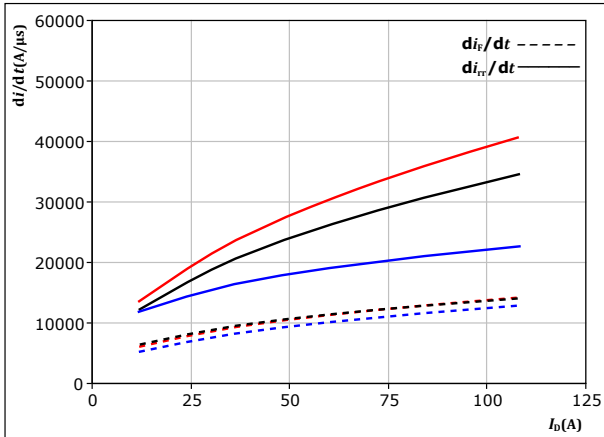
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H-Bridge Switching Characteristics - Lo side

figure 26. MOSFET

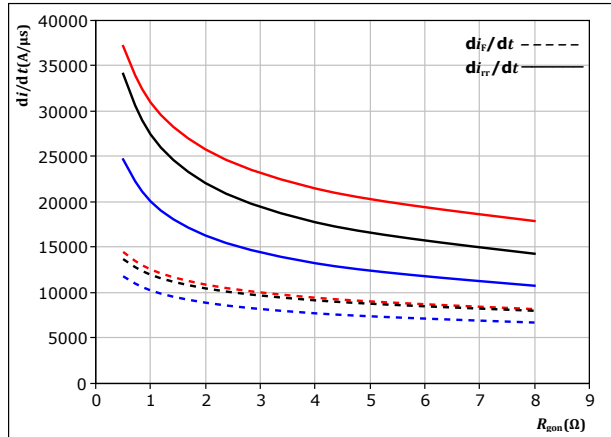
Typical rate of fall of forward and reverse recovery current as a function of drain current
 $di_f/dt, di_r/dt = f(I_D)$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 T_j : 25 °C, 125 °C, 150 °C

figure 27. MOSFET

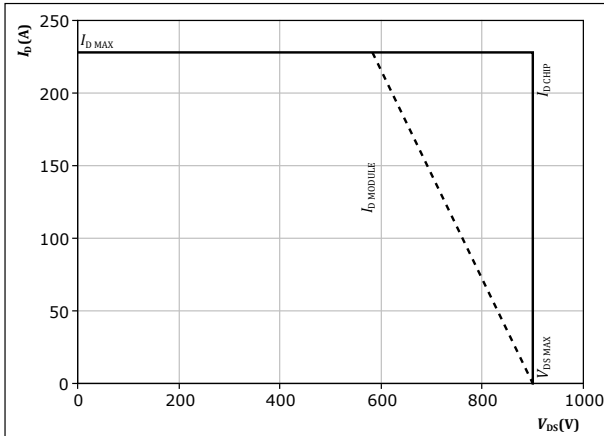
Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_r/dt = f(R_{gon})$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 T_j : 25 °C, 125 °C, 150 °C

figure 28. MOSFET

Reverse bias safe operating area
 $I_D = f(V_{DS})$



At $T_j = 150$ °C
 $R_{gon} = 2$ Ω
 $R_{goff} = 2$ Ω



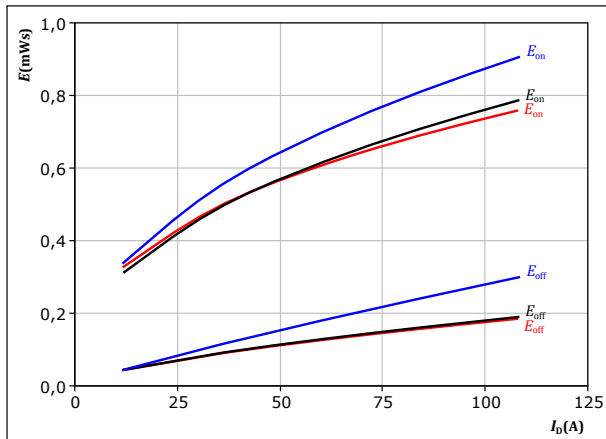
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H-Bridge Switching Characteristics - Hi side

figure 29. MOSFET

Typical switching energy losses as a function of drain current
 $E = f(I_D)$

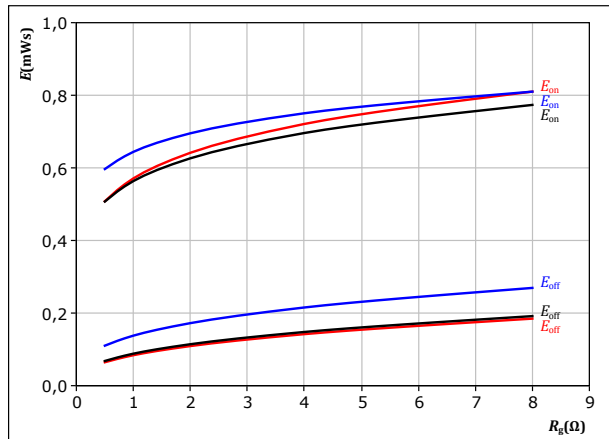


With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 $R_{goff} = 2$ Ω
 $T_j: 25^\circ\text{C}$ (blue), 125°C (black), 150°C (red)

figure 30. MOSFET

Typical switching energy losses as a function of gate resistor
 $E = f(R_g)$

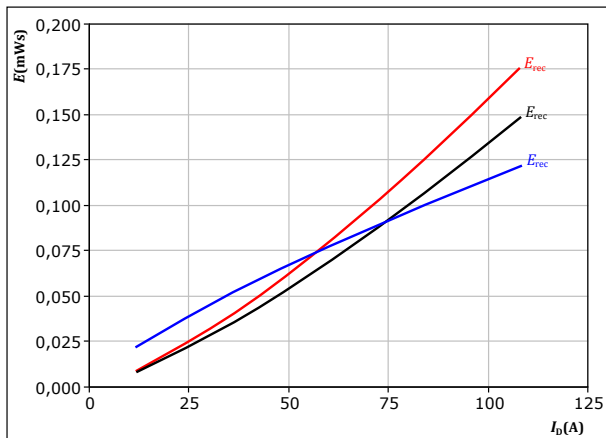


With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 $T_j: 25^\circ\text{C}$ (blue), 125°C (black), 150°C (red)

figure 31. MOSFET

Typical reverse recovered energy loss as a function of drain current
 $E_{rec} = f(I_D)$

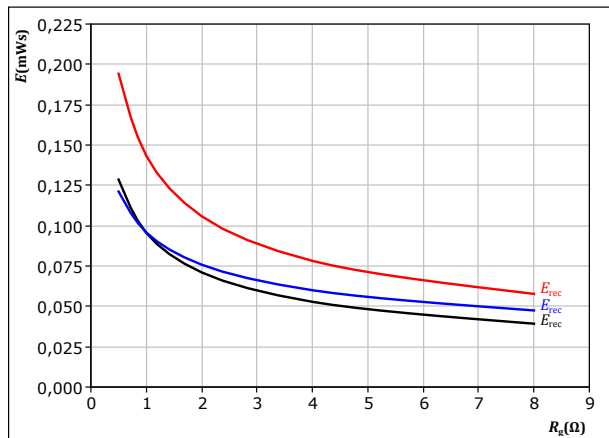


With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 $T_j: 25^\circ\text{C}$ (blue), 125°C (black), 150°C (red)

figure 32. MOSFET

Typical reverse recovered energy loss as a function of gate resistor
 $E_{rec} = f(R_g)$



With an inductive load at

$V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 $T_j: 25^\circ\text{C}$ (blue), 125°C (black), 150°C (red)



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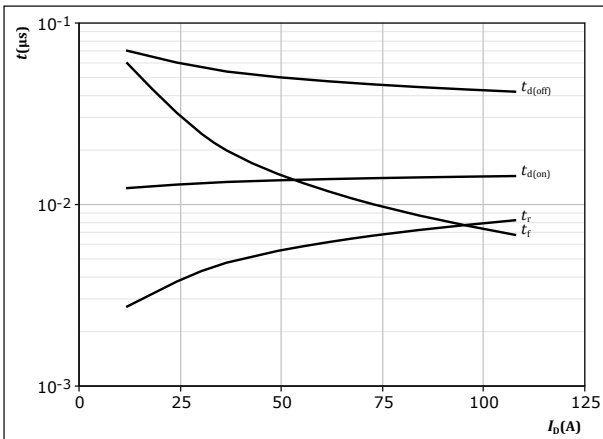
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H-Bridge Switching Characteristics - Hi side

figure 33.

MOSFET

Typical switching times as a function of drain current
 $t = f(I_D)$



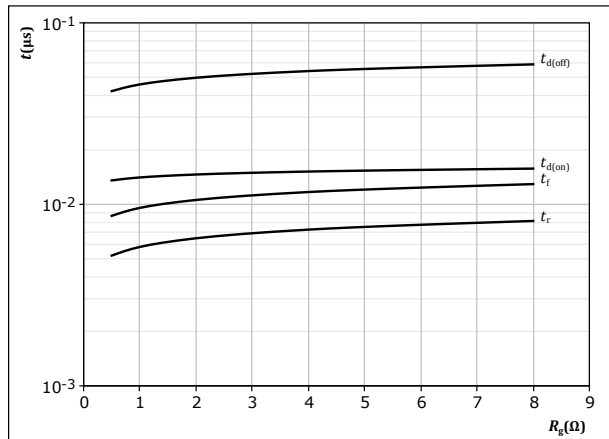
With an inductive load at

$T_j = 150$ °C
 $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 $R_{goff} = 2$ Ω

figure 34.

MOSFET

Typical switching times as a function of gate resistor
 $t = f(R_g)$



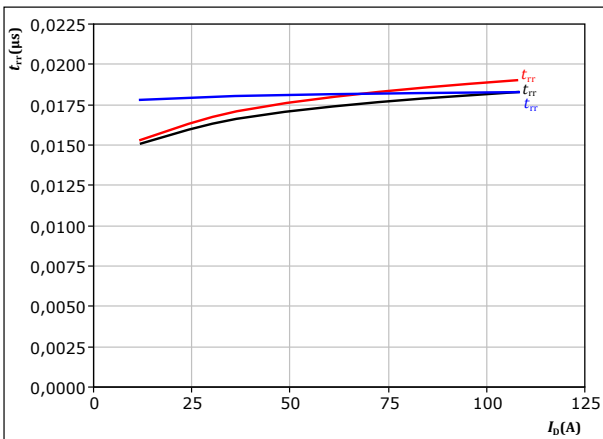
With an inductive load at

$T_j = 150$ °C
 $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A

figure 35.

MOSFET

Typical reverse recovery time as a function of drain current
 $t_{rr} = f(I_D)$



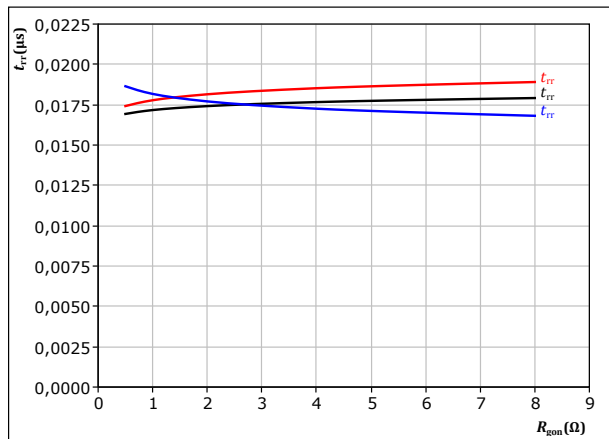
At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω

T_j : — 25 °C
— 125 °C
— 150 °C

figure 36.

MOSFET

Typical reverse recovery time as a function of turn on gate resistor
 $t_{rr} = f(R_{gon})$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A

T_j : — 25 °C
— 125 °C
— 150 °C



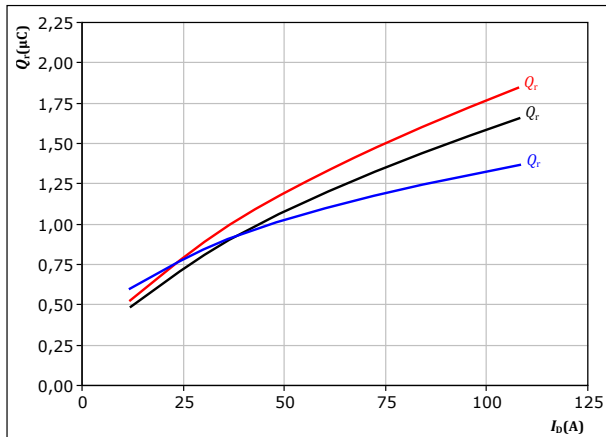
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H-Bridge Switching Characteristics - Hi side

figure 37. MOSFET

Typical recovered charge as a function of drain current

$$Q_r = f(I_D)$$

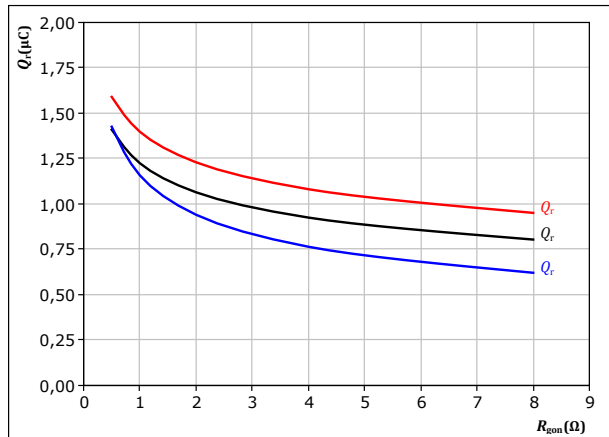


At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 T_j : 25 °C
125 °C
150 °C

figure 38. MOSFET

Typical recovered charge as a function of turn on gate resistor

$$Q_r = f(R_{gon})$$

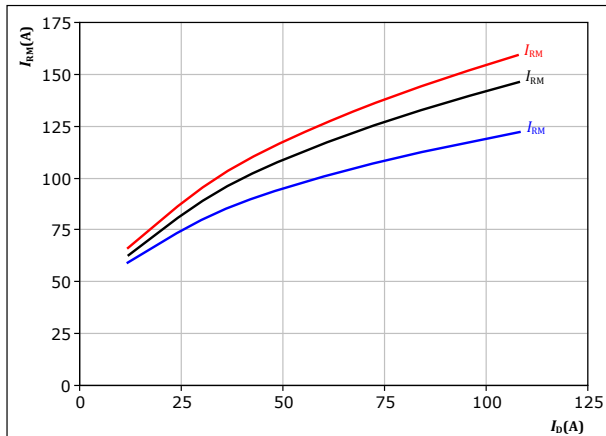


At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 T_j : 25 °C
125 °C
150 °C

figure 39. MOSFET

Typical peak reverse recovery current as a function of drain current

$$I_{RM} = f(I_D)$$

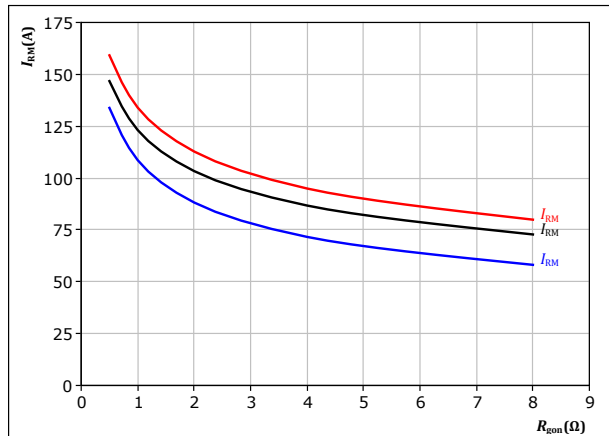


At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 T_j : 25 °C
125 °C
150 °C

figure 40. MOSFET

Typical peak reverse recovery current as a function of turn on gate resistor

$$I_{RM} = f(R_{gon})$$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 T_j : 25 °C
125 °C
150 °C



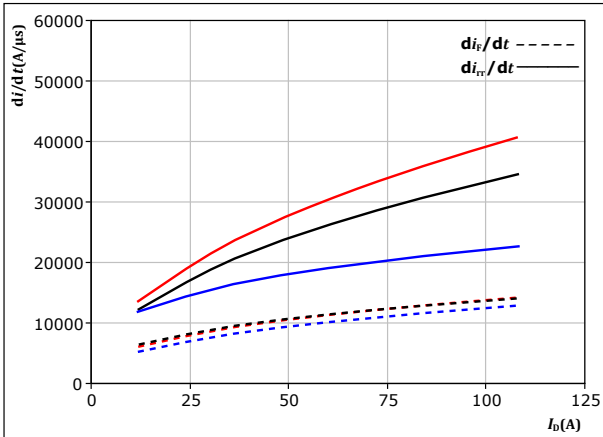
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H-Bridge Switching Characteristics - Hi side

figure 41. MOSFET

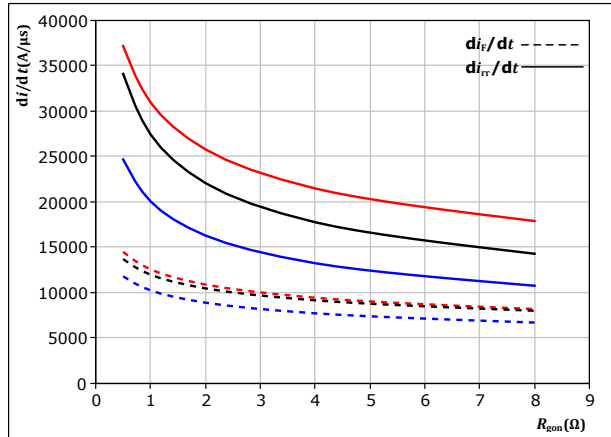
Typical rate of fall of forward and reverse recovery current as a function of drain current
 $di_f/dt, di_{rr}/dt = f(I_D)$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $R_{gon} = 2$ Ω
 T_j : 25 °C, 125 °C, 150 °C

figure 42. MOSFET

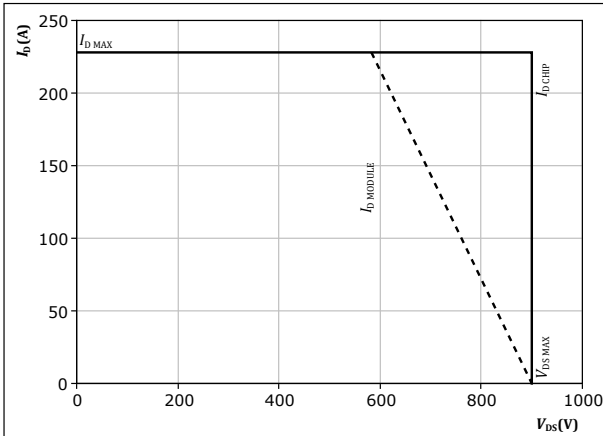
Typical rate of fall of forward and reverse recovery current as a function of turn on gate resistor
 $di_f/dt, di_{rr}/dt = f(R_{gon})$



At $V_{DS} = 600$ V
 $V_{GS} = -5/15$ V
 $I_D = 60$ A
 T_j : 25 °C, 125 °C, 150 °C

figure 43. MOSFET

Reverse bias safe operating area
 $I_D = f(V_{DS})$



At $T_j = 150$ °C
 $R_{gon} = 2$ Ω
 $R_{goff} = 2$ Ω



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Switching Definitions

figure 44. MOSFET

Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

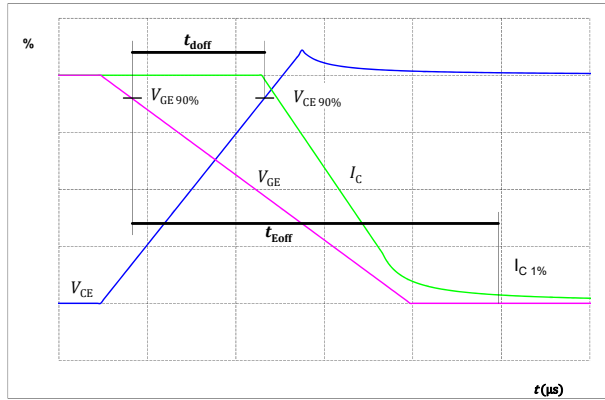


figure 45. MOSFET

Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})

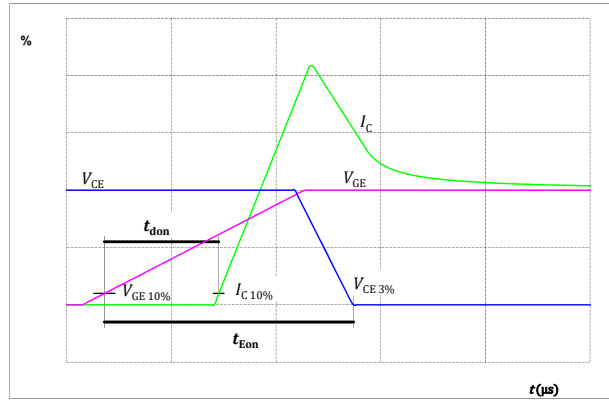


figure 46. MOSFET

Turn-off Switching Waveforms & definition of t_f

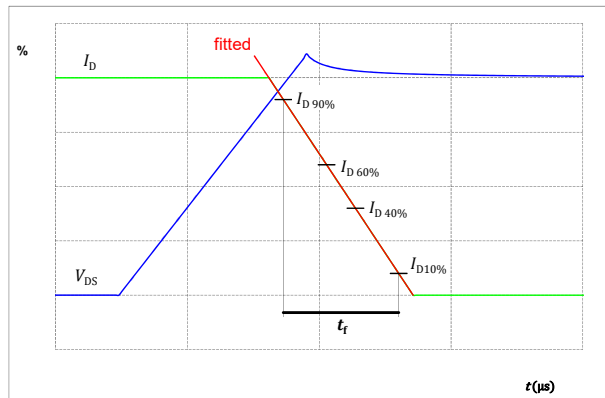
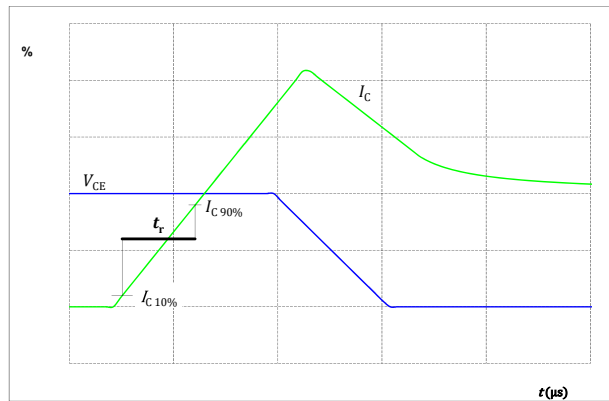


figure 47. MOSFET

Turn-on Switching Waveforms & definition of t_r





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Switching Definitions

figure 48.

FWD

Turn-off Switching Waveforms & definition of t_{tr}

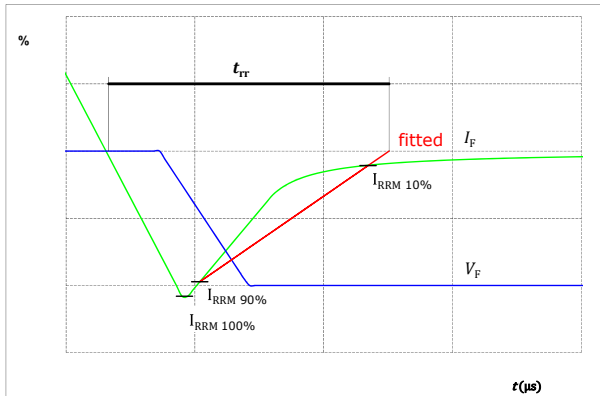


figure 49.

FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)

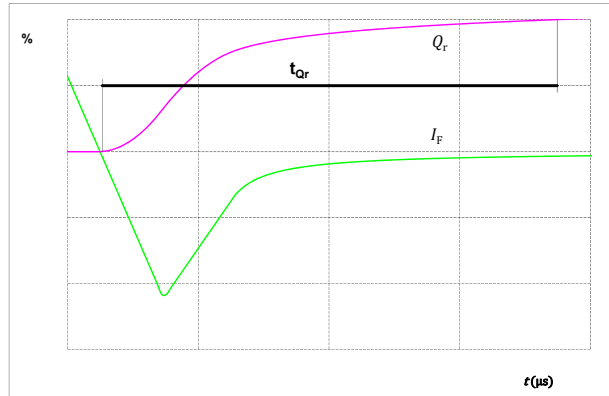
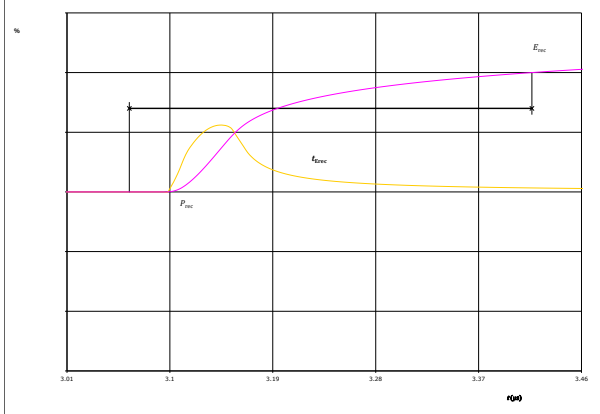


figure 50.

FWD

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})





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datasheet

Ordering Code	
Version	Ordering Code
Without thermal paste	10-FU094PB017ME05-L620F31
With thermal paste	10-FU094PB017ME05-L620F31-/3/

Marking					
	Text	Name NN-NNNNNNNNNNNNNNNN- TTTTTVV	Date code WWYY	UL & VIN UL VIN	Lot LLLLL
	Datamatrix	Type&Ver TTTTTTTV	Lot number LLLLL	Serial SSSS	Date code WWYY

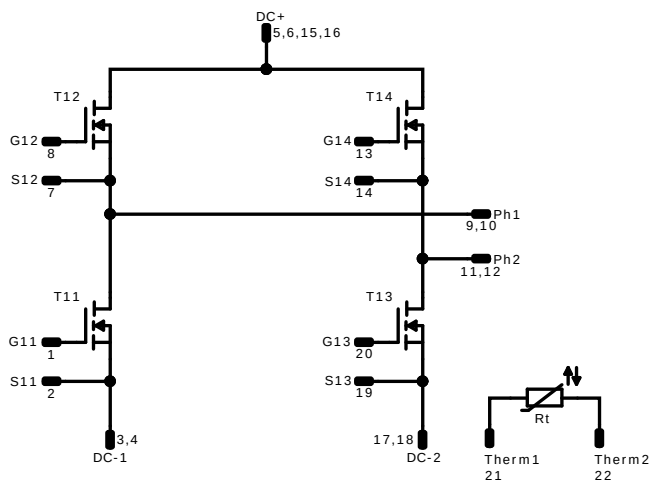
Outline				
Pin table [mm]				Tolerance of pinpositions: ±0.5mm at the end of pins Dimension of coordinate axes is only offset without tolerance
Pin	X	Y	Function	
1	0	22,5	G11	
2	2,9	22,5	S11	
3	8,3	22,5	DC-1	
4	10,8	22,5	DC-1	
5	19,6	22,5	DC+	
6	22,1	22,5	DC+	
7	29,1	22,5	S12	
8	32	22,5	G12	
9	33,5	17,8	Ph1	
10	33,5	15,3	Ph1	
11	33,5	7,2	Ph2	
12	33,5	4,7	Ph2	
13	32	0	G14	
14	29,1	0	S14	
15	22,1	0	DC+	
16	19,6	0	DC+	
17	10,8	0	DC-2	
18	8,3	0	DC-2	
19	2,9	0	S13	
20	0	0	G13	
21	0	8	Therm1	
22	0	14,5	Therm2	



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datasheet

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T11, T13	MOSFET	900 V	21,67 mΩ	H-Bridge Switch - Lo side	
T12, T14	MOSFET	900 V	21,67 mΩ	H-Bridge Switch - Hi side	
Rt	Thermistor			Thermistor	



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Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow 0</i> packages see vincotech.com website.

Package data
Package data for <i>flow 0</i> packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.



Document No.:	Date:	Modification:	Pages
10-FU094PB017ME05-L620F31-D1-14	19 Jun. 2020		

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.